

oxy-silane into said reaction chamber;

supplying electric energy into said reactive gas in order to convert said reactive gas to a plasma; and

depositing a silicon-containing compound on said substrate.

3. (Amended) The method of claims 1 or 2 wherein [said energy is a photo energy] said substrate to be coated with said film has an uneven surface.

In claims 4 and 5, line 1, please change "claim 1" to -- claims 1 or 2 --.

In claim 6, line 1, please change "claim 1" to claim 5 --.

Please add the following new claims:

-- 7. A method for forming a film on a substrate comprising the steps of:

placing a substrate in a reaction chamber;

introducing a first reactive gas comprising a carbon free material;

activating said first reactive gas by supplying energy thereto;

depositing a first layer on said substrate;

introducing a second reactive gas into said reaction chamber after depositing said first layer, said second reactive gas in order to convert said gas to a plasma; and

depositing a silicon oxide film on said first layer.

8. The method of claim 7 wherein said first layer comprises a silicon oxide.